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CONTENTS

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BRIEF REPORTS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

Diamondlike photonic band-gap crystal with a sizable band gap	3517
K. M. Leung	
Temperature dependence of non-Debye disorder in doped manganites	3520
C. Meneghini, R. Cimino, S. Pascarelli, S. Mobilio, C. Raghu, and D. D. Sarma	
Order- N method to calculate the local density of states	3524
Ju Li and Sidney Yip	
Violation of particle number conservation in the GW approximation	3528
Arno Schindlmayr	
Structural and electronic properties of alkaline-earth fluorohalides under pressure	3532
G. Kalpana, B. Palanivel, I. B. Shameem Banu, and M. Rajagopalan	
Electronic structure of indium oxide using cluster calculations	3536
Isao Tanaka, Masataka Mizuno, and Hirohiko Adachi	
Normal Fermi-liquid behavior of quasiholes in the spin-polaron model for copper oxides	3540
G. Jackeli and V. Yu. Yushankhai	
Effective one-band electron-phonon Hamiltonian for nickel perovskites	3544
J. Loos and H. Fehske	
Spin-charge separation in angle-resolved photoemission spectra	3548
Hidekatsu Suzuura and Naoto Nagaosa	
Interrelation between persistent photoconductivity and oxygen order in $\text{GdBa}_2\text{Cu}_3\text{O}_x$ thin films	3552
J. Guimpel, B. Maiorov, E. Osquiguil, G. Nieva, and F. Pardo	

Semiconductors I: bulk

Theoretical studies of native defects in cubic boron nitride	3556
P. Piquini, R. Mota, T. M. Schmidt, and A. Fazzio	
Lattice dynamics of GaN: Effects of $3d$ electrons	3560
K. Karch, F. Bechstedt, and T. Pletl	
Electronic structure of GaN stacking faults	3564
Z. Z. Bandić, T. C. McGill, and Z. Ikonić	
Charge transfer between In and Ga in InGaAs-based alloys	3567
R. Manor, O. Brafman, and R. F. Kopf	

Semiconductors II: surfaces, interfaces, microstructures, and related topics

Quantitative theory of diffraction by carbon nanotubes	3571
Ph. Lambin and A. A. Lucas	
Segregation of boron on the cluster-modeled $\text{Si}(111)\sqrt{3}\times\sqrt{3}R30^\circ$ -B hydrogenated surface	3575
Sanwu Wang, M. W. Radny, and P. V. Smith	
Atomic and electronic structures of rebonded B -type steps on the $\text{Si}(001)$ - 2×1 surface	3579
Takuji Komura, Takafumi Yao, and Masamichi Yoshimura	
Island-size dependence of reconstructed structures on $\text{Si}(111)$	3583
Makoto Itoh	

(Continued)



0163-1829(19970815)56:7;1-S